

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into six groups, D, E, F, G, H and I, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



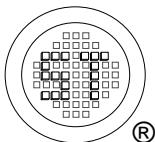
1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	30	mA
Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{\text{CE}} = 5 \text{ V}$, $I_C = 1 \text{ mA}$	h_{FE}	28	-	45	-
	h_{FE}	39	-	60	-
	h_{FE}	54	-	80	-
	h_{FE}	72	-	108	-
	h_{FE}	97	-	146	-
	h_{FE}	132	-	198	-
Collector Base Cutoff Current at $V_{\text{CB}} = 50 \text{ V}$	I_{CBO}	-	-	100	nA
Emitter Base Cutoff Current at $V_{\text{EB}} = 5 \text{ V}$	I_{EBO}	-	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100 \mu\text{A}$	$V_{(\text{BR})\text{CBO}}$	50	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1 \text{ mA}$	$V_{(\text{BR})\text{CEO}}$	30	-	-	V
Emitter Base Breakdown Voltage at $I_E = 100 \mu\text{A}$	$V_{(\text{BR})\text{EBO}}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 10 \text{ mA}$, $I_B = 1 \text{ mA}$	$V_{\text{CE}(\text{sat})}$	-	0.08	0.3	V
Base Emitter Voltage at $V_{\text{CE}} = 5 \text{ V}$, $I_C = 1 \text{ mA}$	$V_{\text{BE}(\text{on})}$	0.60	0.7	0.75	V
Collector Base Capacitance at $V_{\text{CB}} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{cbo}	-	1.5	-	pF
Gain Bandwidth Product at $V_{\text{CE}} = 5 \text{ V}$, $I_C = 1 \text{ mA}$	f_T	150	370	-	MHz

**SEMTECH ELECTRONICS LTD.**ISO/TS 16949 : 2009
Certificate No. 100713000ISO 14001 : 2004
Certificate No. 7116ISO 9001 : 2008
Certificate No. 50713410BS-OHSAS 18001 : 2007
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